



# STD8NS25

## N-CHANNEL 250V - 0.38Ω - 8A DPAK MESH OVERLAY™ MOSFET

PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD8NS25	250 V	< 0.45 Ω	8 A

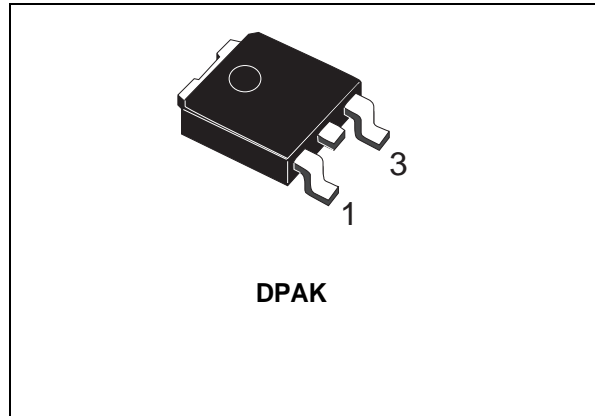
- TYPICAL R<sub>DS(on)</sub> = 0.38 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED

### DESCRIPTION

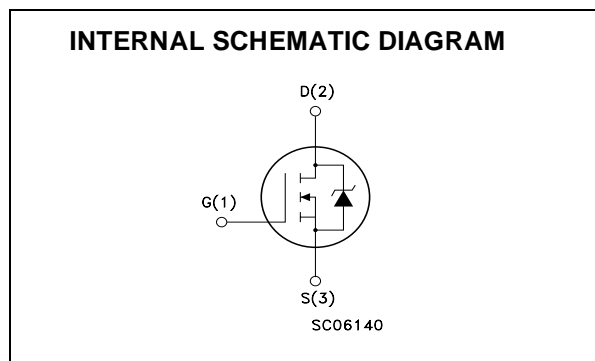
Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performance. The new patented STRIP layout coupled with the Company's proprietary edge termination structure, makes it suitable in converters for lighting applications.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-DC CONVERTERS FOR TELECOM, INDUSTRIAL, AND LIGHTING EQUIPMENT



DPAK



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	250	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	250	V
V <sub>GS</sub>	Gate- source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	8	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	5	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	32	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	80	W
	Derating Factor	0.64	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	209	mJ
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(●)Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 8A, di/dt ≤ 300 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>j</sub>MAX  
(2) Starting T<sub>j</sub> = 25°C, I<sub>AR</sub> = 50A, V<sub>DD</sub> = 20 V

## STD8NS25

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.56	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	8	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	300	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	250			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4 A		0.38	0.45	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 4A	7	8		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		770		pF
C <sub>OSS</sub>	Output Capacitance			118		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			48		pF

## ELECTRICAL CHARACTERISTICS (CONTINUED)

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 125\text{ V}$ , $I_D = 4\text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		13		ns
$t_r$	Rise Time			18		ns
$Q_g$	Total Gate Charge	$V_{DD} = 200\text{ V}$ , $I_D = 8\text{ A}$ , $V_{GS} = 10\text{ V}$		37	50	nC
$Q_{gs}$	Gate-Source Charge			5.2		nC
$Q_{gd}$	Gate-Drain Charge			14.8		nC

## SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(Voff)}$	Turn-off- Delay Time	$V_{DD} = 125\text{ V}$ , $I_D = 4\text{ A}$ , $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		51		ns
$t_f$	Fall Time			16		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{clamp} = 200\text{ V}$ , $I_D = 8\text{ A}$ , $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		12.5		ns
$t_f$	Fall Time			12.5		ns
$t_c$	Cross-over Time			28		ns

## SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				8	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				32	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 8\text{ A}$ , $V_{GS} = 0$			1.7	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ , $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		198		ns
$Q_{rr}$	Reverse Recovery Charge			1.1		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			11.3		A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

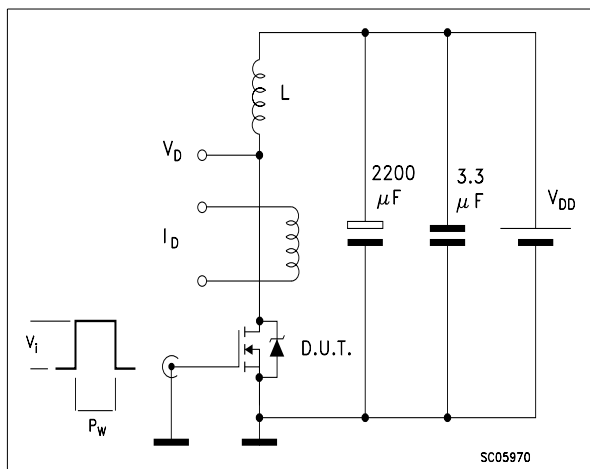


Fig. 2: Unclamped Inductive Waveform

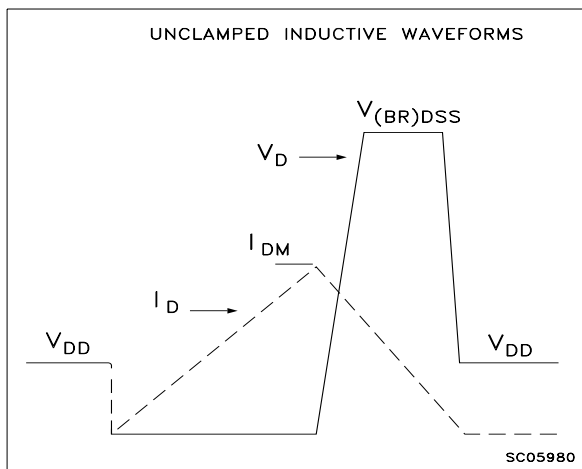


Fig. 3: Switching Times Test Circuit For Resistive Load

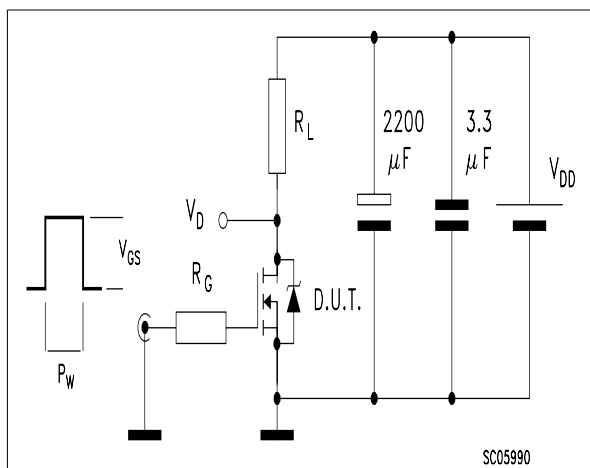


Fig. 4: Gate Charge test Circuit

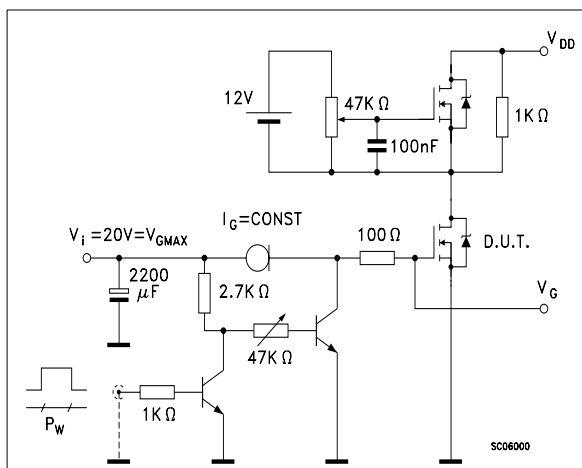
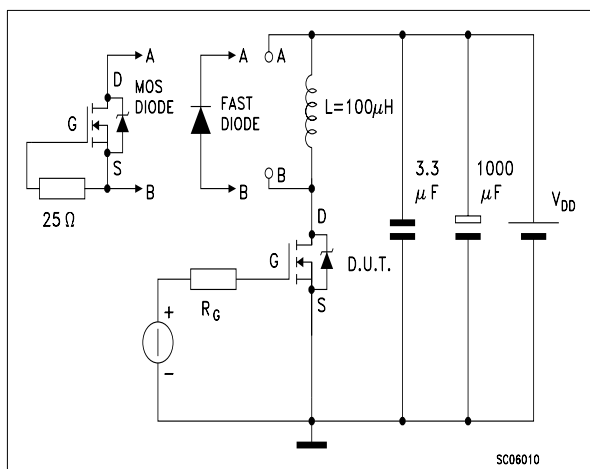
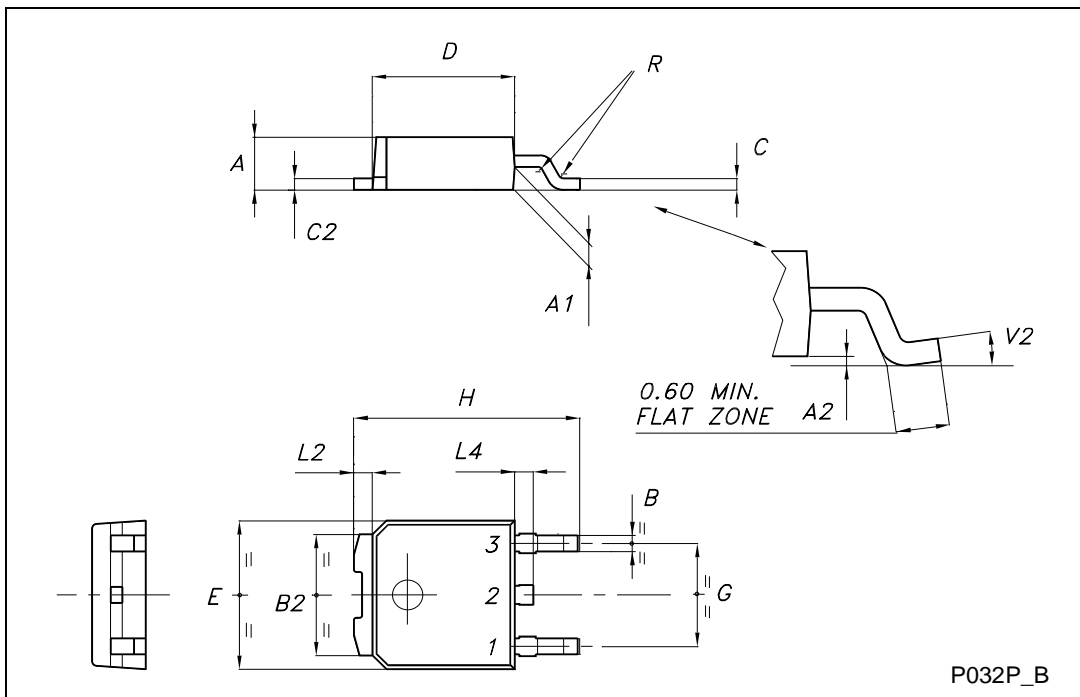


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2001 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco -  
Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

<http://www.st.com>